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# FPF2C8P2NL07A

## F2, 3-phase, 3-level NPC module with Press-fit / NTC

### General Description

Fairchild's new inverter modules provide low conduction and switching loss as well. And Press-Fit technology provides simple and reliable mounting. These modules are optimized for the applications such as solar inverter and UPS where a high efficiency and robust design is needed.

### Electrical Features

- High Efficiency
- Low Conduction and Switching Losses
- Field Stop IGBT for Inner and Outer Switch
- STEALTH™ Diode for Path Diode
- Built-in NTC for Temperature Monitoring

### Mechanical Features

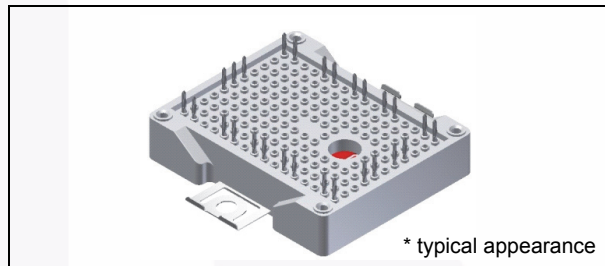
- Compact Size : F2 Package
- Press-fit Contact Technology
- Al<sub>2</sub>O<sub>3</sub> Substrate with Low Thermal Resistance

### Applications

- Solar Inverter
- UPS

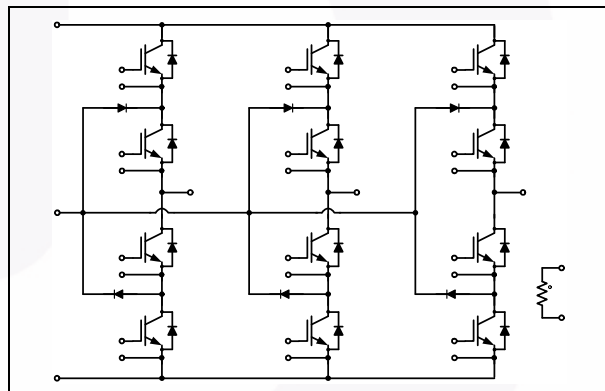
### Related Materials

- AN-4167: Mounting Guideline for F1 / F2 Modules with Press-Fit Pins



\* typical appearance

Package Code: F2



Internal Circuit Diagram

### Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity / Tray
FPF2C8P2NL07A	FPF2C8P2NL07A	F2	Tray	14

FPF2C8P2NL07A - F2, 3-phase, 3-level NPC module with Press-fit / NTC

**Absolute Maximum Ratings**  $T_C = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Description	Rating	Units
<b>Outer IGBT(Q1, Q4, Q5, Q8, Q9, Q12)</b>			
$V_{CES}$	Collector-Emitter Voltage	650	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Continuous Collector Current @ $T_C = 80^\circ\text{C}$ , $T_{Jmax} = 175^\circ\text{C}$	30	A
$I_{CM}$	Pulsed Collector Current limited by $T_{Jmax}$	60	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	135	W
$T_J$	Operating Junction Temperature	- 40 to + 150	$^\circ\text{C}$
<b>Inner IGBT(Q2, Q3, Q6, Q7, Q10, Q11)</b>			
$V_{CES}$	Collector-Emitter Voltage	650	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Continuous Collector Current @ $T_C = 80^\circ\text{C}$ , $T_{Jmax} = 175^\circ\text{C}$	50	A
$I_{CM}$	Pulsed Collector Current limited by $T_{Jmax}$	100	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	174	W
$T_J$	Operating Junction Temperature	- 40 to + 150	$^\circ\text{C}$
<b>Outer - Inner IGBT Series Connection</b>			
SCWT	Short Circuit Withstand Time $V_{DC} = 300\text{ V}$ , $V_{GE} = 15\text{ V}$ $T_C = 25^\circ\text{C}$	4	$\mu\text{S}$
<b>Diode</b>			
$V_{RRM}$	Peak Repetitive Reverse Voltage	650	V
$I_F$	Continuous Forward Current @ $T_C = 80^\circ\text{C}$ , $T_{Jmax} = 175^\circ\text{C}$	15	A
$I_{FM}$	Maximum Forward Current	30	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	100	W
$T_J$	Operating Junction Temperature	- 40 to + 150	$^\circ\text{C}$
<b>Module</b>			
$T_{STG}$	Storage Temperature	- 40 to + 125	$^\circ\text{C}$
$V_{ISO}$	Isolation Voltage @ AC 1 min.	2500	V
Iso_Material	Internal Isolation Material	$\text{Al}_2\text{O}_3$	
$T_{MOUNT}$	Mounting Torque	2.0 to 5.0	Nm
Creepage	Terminal to Heat Sink	11.5	mm
	Terminal to Terminal	6.3	mm
Clearance	Terminal to Heat Sink	10.0	mm
	Terminal to Terminal	5.0	mm

**Electrical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted.

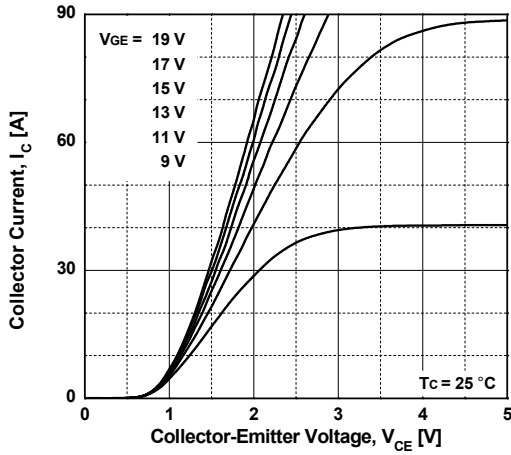
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units	
<b>Outer IGBT</b>							
<b>Off Characteristics</b>							
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	650	-	-	V	
$I_{CES}$	Collector Cut-off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	$\mu\text{A}$	
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	2	$\mu\text{A}$	
<b>On Characteristics</b>							
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 30\text{ mA}$	4.5	5.6	6.7	V	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}$	-	1.55	2.2	V	
		$I_C = 30\text{ A}, V_{GE} = 15\text{ V} @ T_C = 125^\circ\text{C}$	-	1.75	-	V	
		$I_C = 60\text{ A}, V_{GE} = 15\text{ V}$	-	2.13	-	V	
<b>Switching Characteristics</b>							
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300\text{ V}$ $I_C = 30\text{ A}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 20\ \Omega$ Inductive Load $T_C = 25^\circ\text{C}$	-	33	-	ns	
$t_r$	Rise Time		-	43	-	ns	
$t_{d(off)}$	Turn-Off Delay Time		-	197	-	ns	
$t_f$	Fall Time		-	17	-	ns	
$E_{ON}$	Turn-On Switching Loss per Pulse		-	0.68	-	mJ	
$E_{OFF}$	Turn-Off Switching Loss per Pulse		-	0.38	-	mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC} = 300\text{ V}$ $I_C = 30\text{ A}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 20\ \Omega$ Inductive Load $T_C = 125^\circ\text{C}$	-	29	-	ns
$t_r$	Rise Time			-	50	-	ns
$t_{d(off)}$	Turn-Off Delay Time			-	205	-	ns
$t_f$	Fall Time			-	25	-	ns
$E_{ON}$	Turn-On Switching Loss per Pulse	-		0.86	-	mJ	
$E_{OFF}$	Turn-Off Switching Loss per Pulse	-		0.52	-	mJ	
$Q_g$	Total Gate Charge	$V_{CC} = 300\text{ V}, I_C = 30\text{ A}, V_{GE} = \pm 15\text{ V}$		-	0.26	-	$\mu\text{C}$
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip		-	-	1.11	$^\circ\text{C/W}$
<b>Inner IGBT</b>							
<b>Off Characteristics</b>							
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	650	-	-	V	
$I_{CES}$	Collector Cut-off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	$\mu\text{A}$	
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	2	$\mu\text{A}$	
<b>On Characteristics</b>							
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 50\text{ mA}$	4.5	5.6	6.7	V	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	-	1.65	2.3	V	
		$I_C = 50\text{ A}, V_{GE} = 15\text{ V} @ T_C = 125^\circ\text{C}$	-	1.95	-	V	
		$I_C = 100\text{ A}, V_{GE} = 15\text{ V}$	-	2.49	-	V	
<b>Switching Characteristics</b>							
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300\text{ V}$ $I_C = 50\text{ A}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 15\ \Omega$ Inductive Load $T_C = 25^\circ\text{C}$	-	41	-	ns	
$t_r$	Rise Time		-	65	-	ns	
$t_{d(off)}$	Turn-Off Delay Time		-	233	-	ns	
$t_f$	Fall Time		-	18	-	ns	
$E_{ON}$	Turn-On Switching Loss per Pulse		-	0.87	-	mJ	
$E_{OFF}$	Turn-Off Switching Loss per Pulse		-	0.77	-	mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC} = 300\text{ V}$ $I_C = 50\text{ A}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 15\ \Omega$ Inductive Load $T_C = 125^\circ\text{C}$	-	39	-	ns
$t_r$	Rise Time			-	76	-	ns
$t_{d(off)}$	Turn-Off Delay Time			-	243	-	ns
$t_f$	Fall Time			-	20	-	ns
$E_{ON}$	Turn-On Switching Loss per Pulse	-		0.99	-	mJ	
$E_{OFF}$	Turn-Off Switching Loss per Pulse	-		0.93	-	mJ	
$Q_g$	Total Gate Charge	$V_{CC} = 300\text{ V}, I_C = 50\text{ A}, V_{GE} = \pm 15\text{ V}$		-	0.39	-	nC
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip		-	-	0.86	$^\circ\text{C/W}$

**Electrical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted.

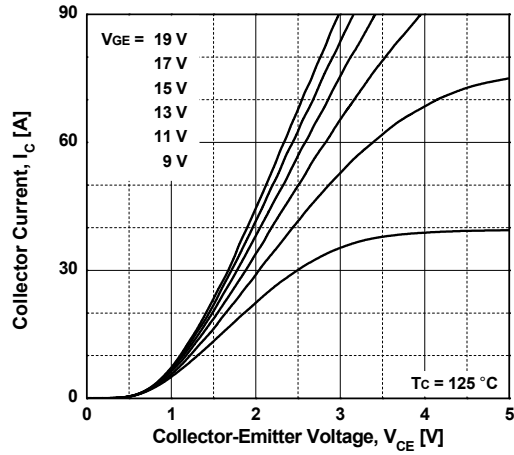
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
<b>Diode</b>						
$V_{FM}$	Diode Forward Voltage	$I_F = 15\text{ A}$	-	2.55	3.4	V
		$I_F = 15\text{ A @ }T_C = 125^\circ\text{C}$	-	1.78	-	V
$I_R$	Reverse Leakage Current	$V_R = 650\text{ V}$	-	-	250	$\mu\text{A}$
$t_{rr}$	Reverse Recovery Time	$V_R = 300\text{ V}, I_F = 15\text{ A}$ $di_F / dt = 700\text{ A/us}$ $T_C = 25^\circ\text{C}$	-	23	-	ns
$I_{rr}$	Reverse Recovery Current		-	9.9	-	A
$Q_{rr}$	Reverse Recovery Charge		-	113	-	nC
$t_{rr}$	Reverse Recovery Time	$V_R = 300\text{ V}, I_F = 15\text{ A}$ $di_F / dt = 700\text{ A/us}$ $T_C = 125^\circ\text{C}$	-	49	-	ns
$I_{rr}$	Reverse Recovery Current		-	15.2	-	A
$Q_{rr}$	Reverse Recovery Charge		-	366	-	nC
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip	-	-	1.44	$^\circ\text{C/W}$
<b>NTC_ Thermistor</b>						
$R_{NTC}$	Rated Resistance	$T_C = 25^\circ\text{C}$	-	5.0	-	k $\Omega$
		$T_C = 100^\circ\text{C}$	-	493	-	$\Omega$
	Tolerance	$T_C = 25^\circ\text{C}$	- 5	-	+ 5	%
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	-	-	20	mW
$B_{Value}$	B-Constant	$B_{25/50}$	-	3375	-	K
		$B_{25/100}$	-	3436	-	K

## Typical Performance Characteristic

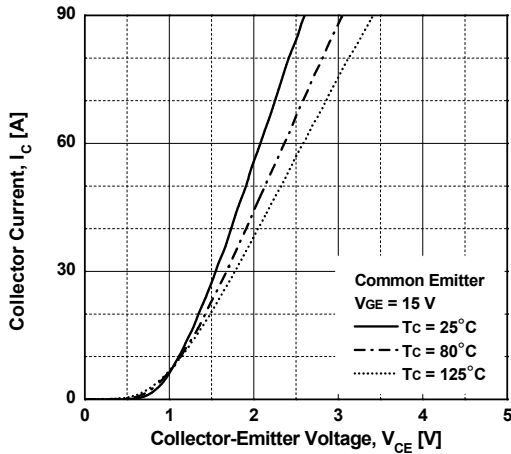
**Fig 1. Typical Output Characteristics - Outer IGBT**



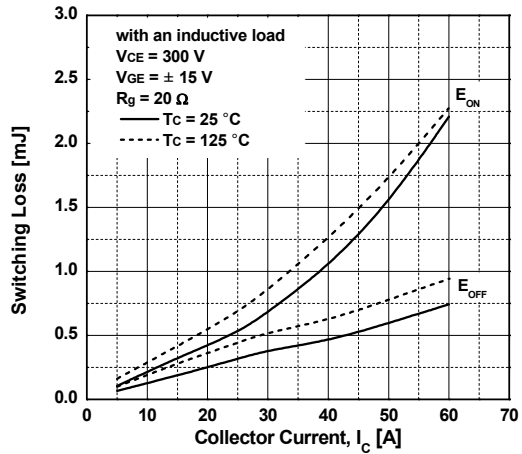
**Fig 2. Typical Output Characteristics - Outer IGBT**



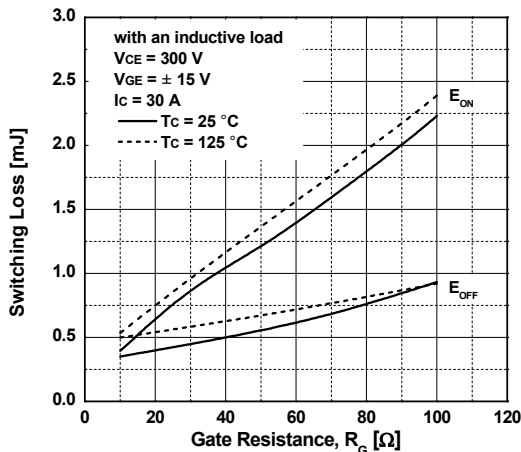
**Fig 3. Typical Saturation Voltage Characteristics - Outer IGBT**



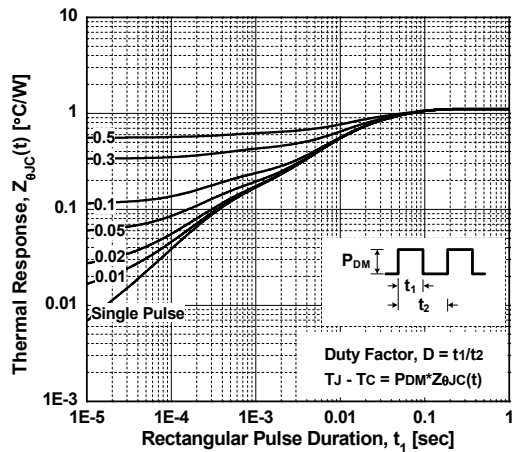
**Fig 4. Switching Loss vs. Collector Current - Outer IGBT**



**Fig 5. Switching Loss vs. Gate Resistance - Outer IGBT**



**Fig 6. Transient Thermal Impedance - Outer IGBT**



## Typical Performance Characteristic

Fig 7. Typical Output Characteristics - Inner IGBT

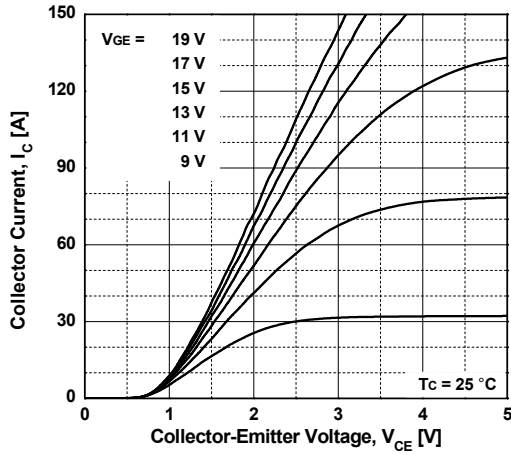


Fig 8. Typical Output Characteristics - Inner IGBT

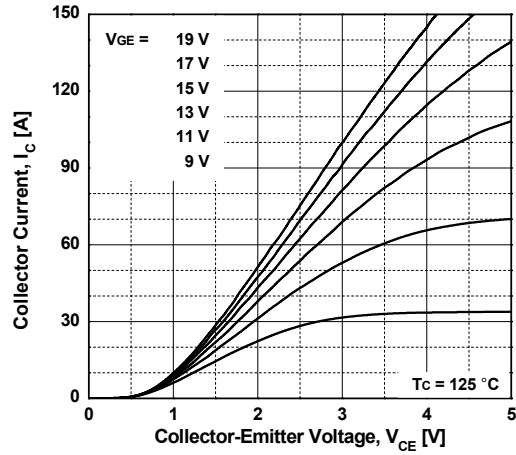


Fig 9. Typical Saturation Voltage Characteristics - Inner IGBT

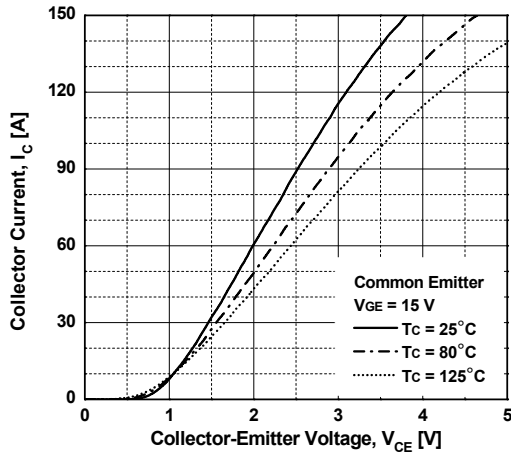


Fig 10. Switching Loss vs. Collector Current - Inner IGBT

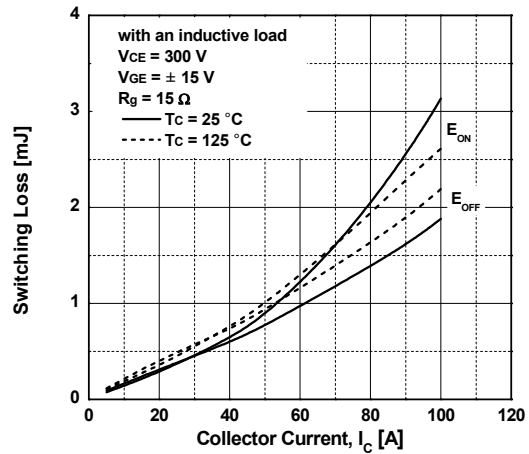


Fig 11. Switching Loss vs. Gate Resistance - Inner IGBT

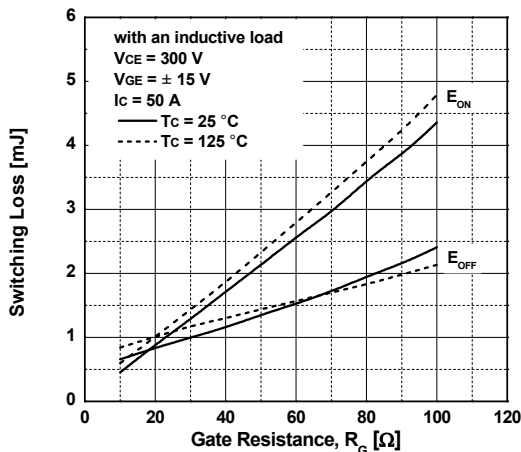
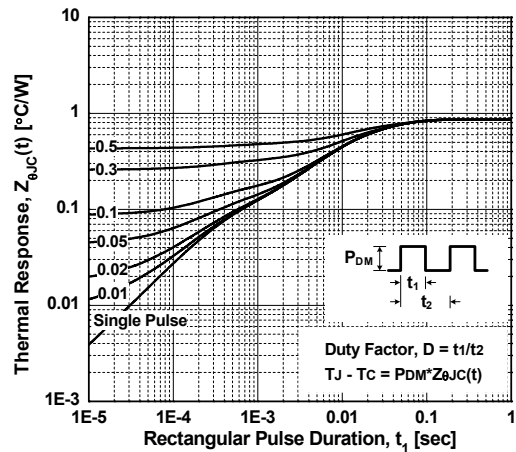
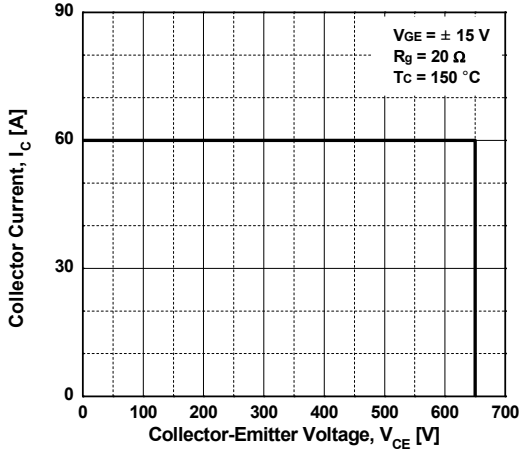


Fig 12. Transient Thermal Impedance - Inner IGBT

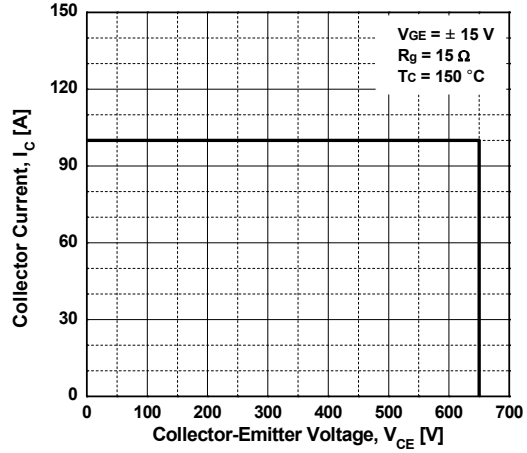


## Typical Performance Characteristic

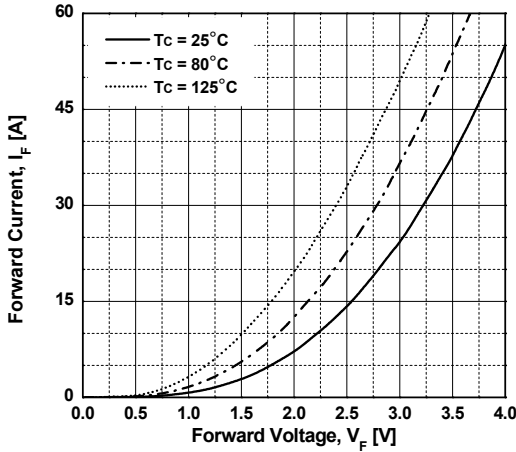
**Fig 13. Reverse Bias Safe Operating Area (RBSOA) - Outer IGBT**



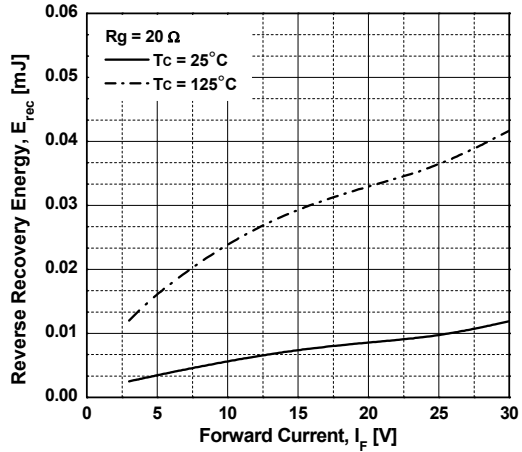
**Fig 14. Reverse Bias Safe Operating Area (RBSOA) - Inner IGBT**



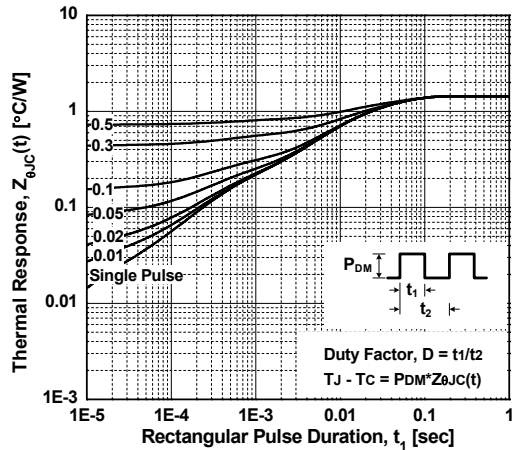
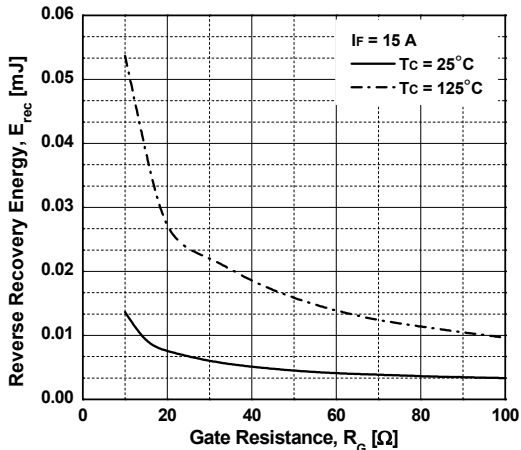
**Fig 15. Typical Forward Voltage Drop - Diode**



**Fig 16. Reverse Recovery Energy vs. Forward Current - Diode**

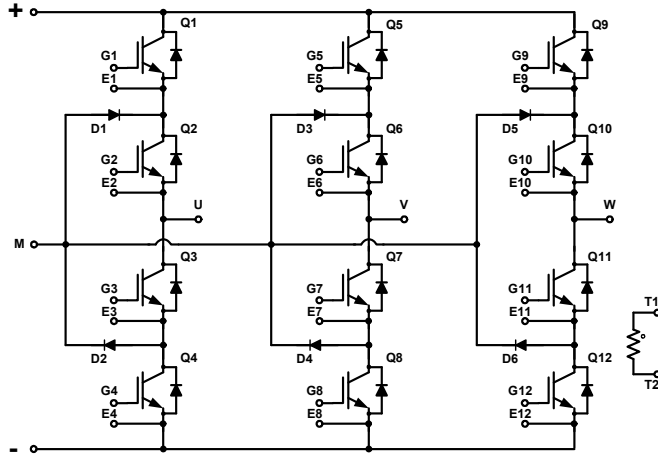


**Fig 17. Reverse Recovery Energy vs. Gate Resistance - Diode**      **Fig 18. Transient Thermal Impedance - Diode**

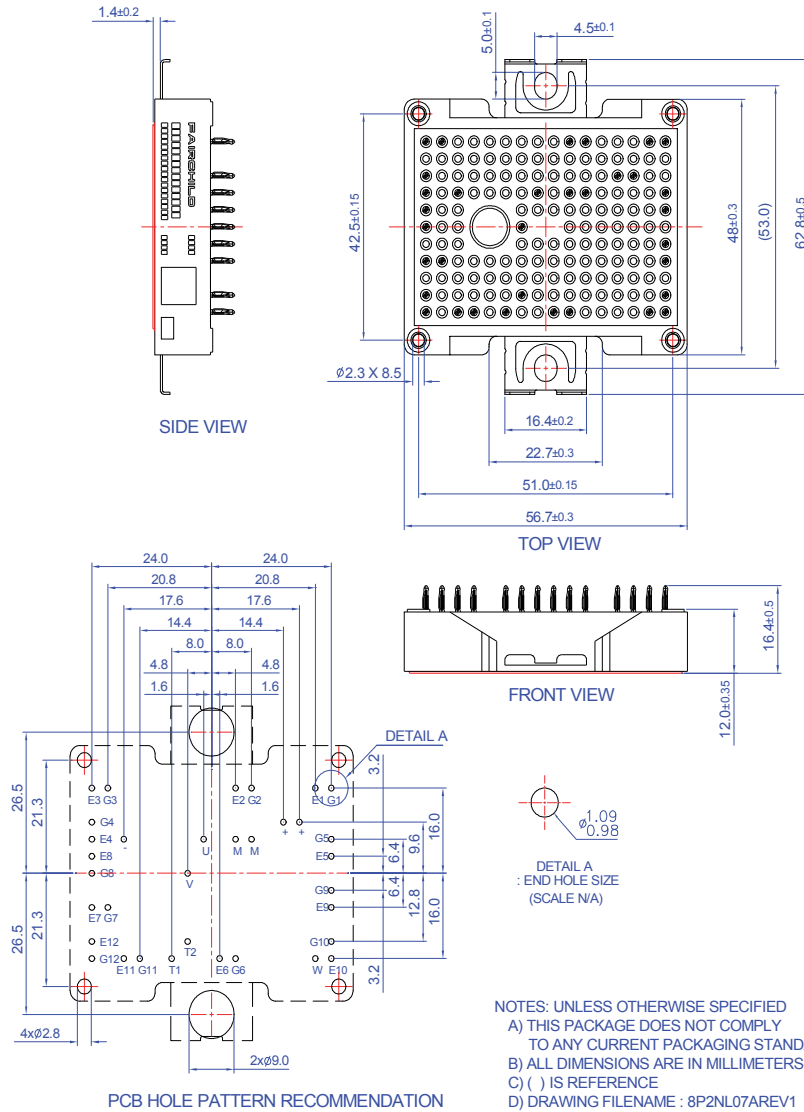




### Internal Circuit Diagram



### Package Outlines [mm]



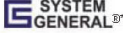



- PIN-GRID 3.2mm  
 - TOLERANCE OF PCB HOLE PATTERN  $\pm 0.1$





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**Definition of Terms**

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